

**PNP Darlington transistors****BSR60; BSR61; BSR62****FEATURES**

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

**APPLICATIONS**

- Industrial applications such as:
  - Print hammer
  - Solenoid
  - Relay and lamp driving.

**DESCRIPTION**

PNP Darlington transistor in a TO-92; SOT54 plastic package. NPN complements: BSR50, BSR51 and BSR52.

**PINNING**

PIN	DESCRIPTION
1	base
2	collector
3	emitter

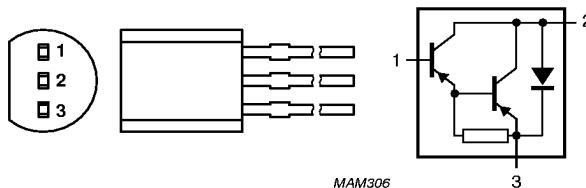


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CBO}$	collector-base voltage BSR60 BSR61 BSR62	open emitter	–	–	-60	V
$V_{CES}$	collector-emitter voltage BSR60 BSR61 BSR62	$V_{BE} = 0$	–	–	-45	V
$I_C$	collector current (DC)		–	–	-1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25^\circ C$	–		0.83	W
$h_{FE}$	DC current gain	$I_C = -150 \text{ mA}; V_{CE} = -10 \text{ V}$	1000	–	–	
		$I_C = -500 \text{ mA}; V_{CE} = -10 \text{ V}$	2000	–	–	
$f_T$	transition frequency	$I_C = -500 \text{ mA}; V_{CE} = -5 \text{ V}; f = 100 \text{ MHz}$	–	200	–	MHz

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage BSR60 BSR61 BSR62	open emitter	—	-60	V
			—	-80	V
			—	-90	V
$V_{CES}$	collector-emitter voltage BSR60 BSR61 BSR62	$V_{BE} = 0$	—	-45	V
			—	-60	V
			—	-80	V
$V_{EBO}$	emitter-base voltage	open collector	—	-5	V
$I_c$	collector current (DC)		—	-1	A
$I_{CM}$	peak collector current		—	-2	A
$I_B$	base current (DC)		—	-0.2	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$ ; note 1	—	0.83	W
$T_{stg}$	storage temperature		-65	+150	$^\circ\text{C}$
$T_j$	junction temperature		—	150	$^\circ\text{C}$
$T_{amb}$	operating ambient temperature		-65	+150	$^\circ\text{C}$

**Note**

- Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	150	K/W

**Note**

- Transistor mounted on an FR4 printed-circuit board.

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**CHARACTERISTICS** $T_j = 25^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$	collector cut-off current BSR60 BSR61 BSR62	$V_{BE} = 0$ ; $V_{CE} = -45\text{ V}$	—	—	-50	nA
		$V_{BE} = 0$ ; $V_{CE} = -60\text{ V}$	—	—	-50	nA
		$V_{BE} = 0$ ; $V_{CE} = -80\text{ V}$	—	—	-50	nA
$I_{EBO}$	emitter cut-off current	$I_C = 0$ ; $V_{EB} = -4\text{ V}$	—	—	-50	nA
$h_{FE}$	DC current gain	$V_{CE} = -10\text{ V}$ ; see Fig.2	1000	—	—	
		$I_C = -150\text{ mA}$				
		$I_C = -500\text{ mA}$	2000	—	—	
$V_{CEsat}$	collector-emitter saturation voltage BSR60; BSR61 BSR62	$I_C = -0.5\text{ A}$ ; $I_B = -0.5\text{ mA}$	—	—	-1.3	V
			—	—	-1.4	V
$V_{CEsat}$	collector-emitter saturation voltage BSR60 BSR61 BSR62	$I_C = -1\text{ A}$ ; $I_B = -4\text{ mA}$	—	—	-1.6	V
		$I_C = -1\text{ A}$ ; $I_B = -1\text{ mA}$	—	—	-1.6	V
		$I_C = -1\text{ A}$ ; $I_B = -4\text{ mA}$	—	—	-1.8	V
$V_{BEsat}$	base-emitter saturation voltage BSR60; BSR61 BSR62	$I_C = -0.5\text{ A}$ ; $I_B = -0.5\text{ mA}$	—	—	-1.9	V
			—	—	-2	V
$V_{BEsat}$	base-emitter saturation voltage BSR60 BSR61 BSR62	$I_C = -1\text{ A}$ ; $I_B = -4\text{ mA}$	—	—	-2.2	V
		$I_C = -1\text{ A}$ ; $I_B = -1\text{ mA}$	—	—	-2.2	V
		$I_C = -1\text{ A}$ ; $I_B = -4\text{ mA}$	—	—	-2.4	V
$f_T$	transition frequency	$I_C = -500\text{ mA}$ ; $V_{CE} = -5\text{ V}$ ; $f = 100\text{ MHz}$	—	200	—	MHz
<b>Switching times (between 10% and 90% levels); see Fig.3</b>						
$t_{on}$	turn-on time	$I_{Con} = -500\text{ mA}$ ; $I_{Bon} = -0.5\text{ mA}$ ; $I_{Boff} = 0.5\text{ mA}$	—	—	0.5	$\mu\text{s}$
$t_{off}$	turn-off time		—	—	0.7	$\mu\text{s}$

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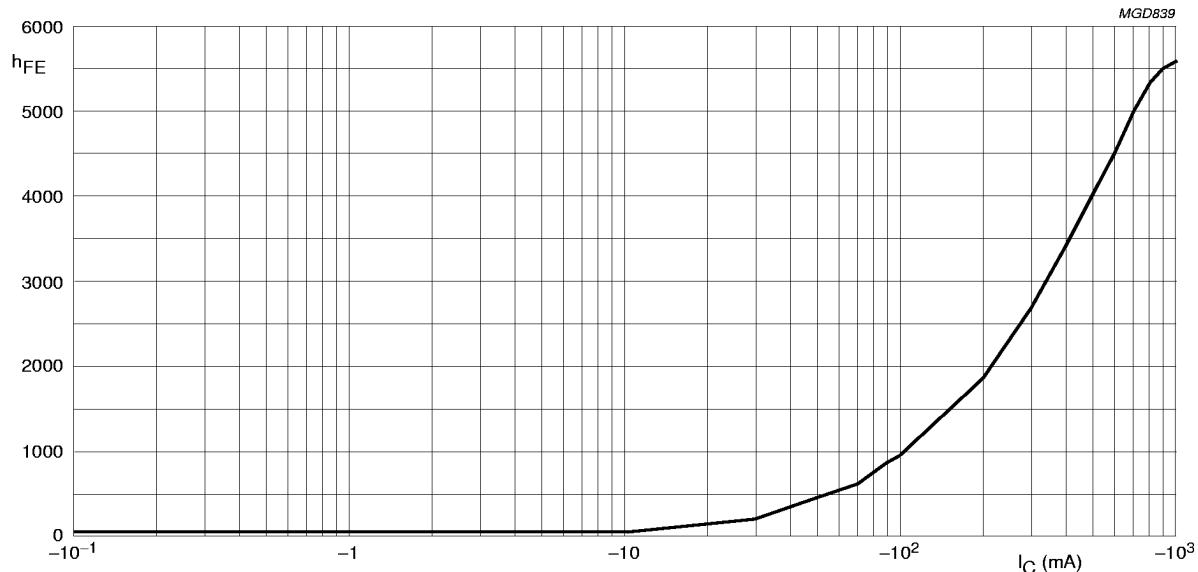
 $V_{CE} = -10$  V.

Fig.2 DC current gain; typical values.

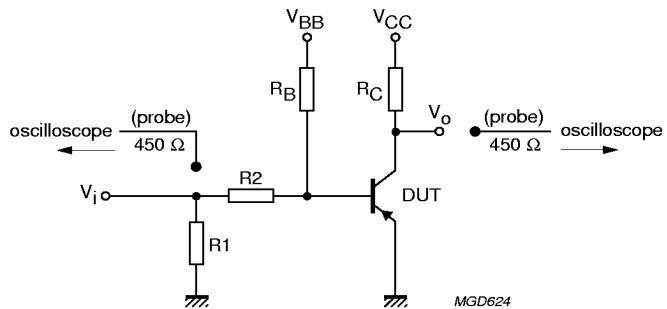
 $V_i = -10$  V;  $T = 200$   $\mu$ s;  $t_p = 6$   $\mu$ s;  $t_r = t_f \leq 3$  ns. $R1 = 56$   $\Omega$ ;  $R2 = 10$  k $\Omega$ ;  $R_B = 10$  k $\Omega$ ;  $R_C = 18$   $\Omega$ . $V_{BB} = 1.8$  V;  $V_{CC} = -10.7$  V.Oscilloscope: input impedance  $Z_i = 50$   $\Omega$ .

Fig.3 Test circuit for switching times.

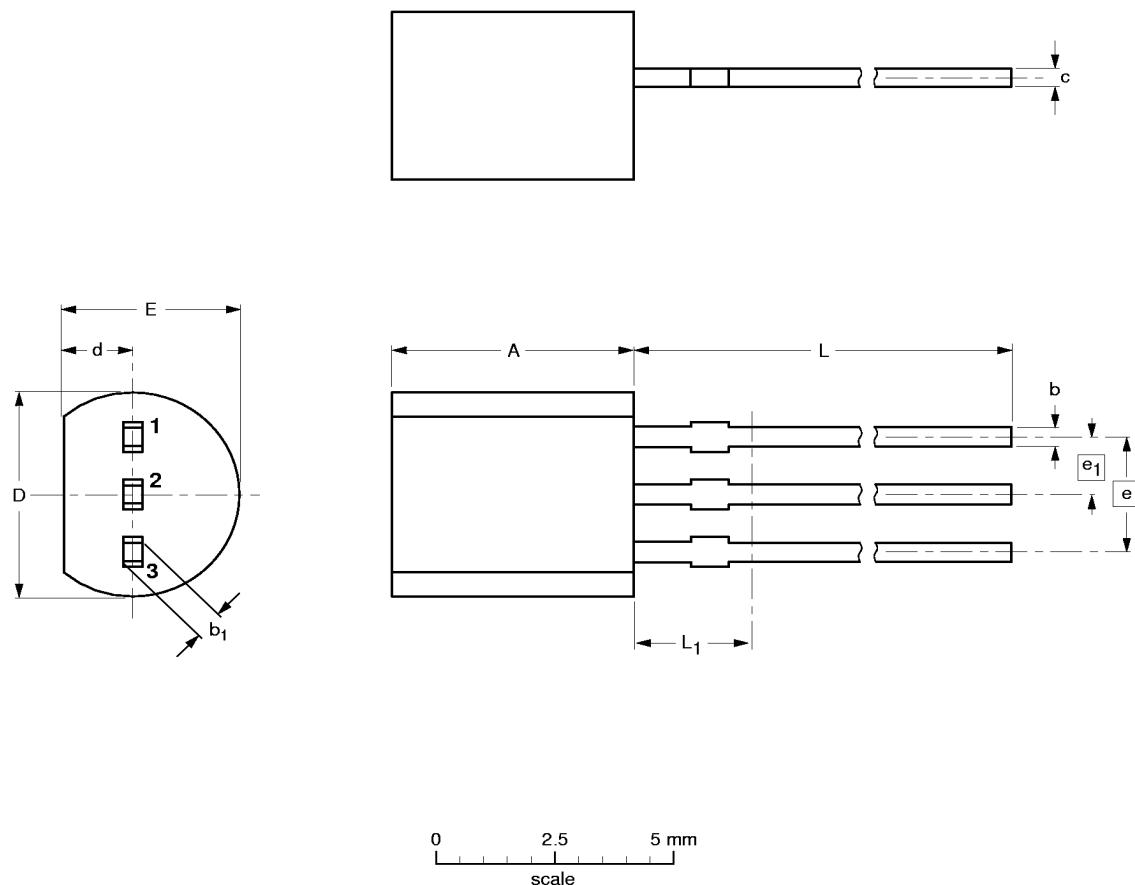
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## PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



## DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

## Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT54		TO-92	SC-43			97-02-28